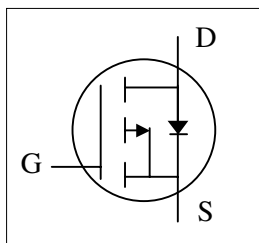




- ▼ Low Gate Charge
- ▼ Simple Drive Requirement
- ▼ Fast Switching

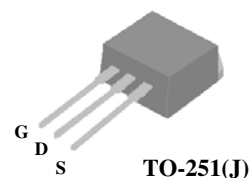
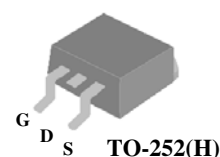


BV_{DSS}	-30V
$R_{DS(ON)}$	50m Ω
I_D	- 20A

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The TO-252/TO-251 package is widely used for commercial-industrial application.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
V_{GS}	Gate-Source Voltage	+20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	- 20	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	-13	A
I_{DM}	Pulsed Drain Current ¹	-60	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	12.5	W
	Linear Derating Factor	0.1	W/ $^{\circ}C$
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	10	$^{\circ}C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	62.5	$^{\circ}C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	$^{\circ}C/W$



Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-10A	-	-	50	mΩ
		V _{GS} =-4.5V, I _D =-5A	-	-	90	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-10A	-	10	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T _j =125°C)	V _{DS} =-24V, V _{GS} =0V	-	-	-250	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =± 20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =-10A	-	8	16	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-24V	-	1.6	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	4.3	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-15V	-	6.3	-	ns
t _r	Rise Time	I _D =-10A	-	46	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =-10V	-	20	-	ns
t _f	Fall Time	R _D =1.5Ω	-	7.4	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	570	740	pF
C _{oss}	Output Capacitance	V _{DS} =-25V	-	80	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	75	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-5A, V _{GS} =0V	-	-	-1.3	V
t _{rr}	Reverse Recovery Time ²	I _S =-10A, V _{GS} =0V,	-	18	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	10	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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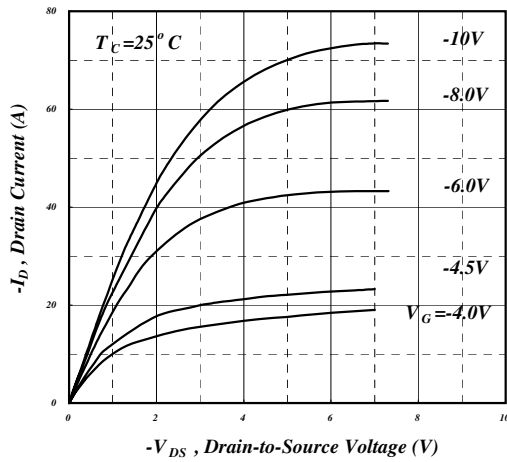


Fig 1. Typical Output Characteristics

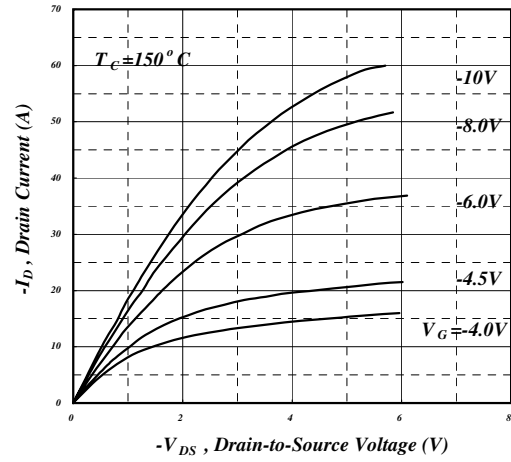


Fig 2. Typical Output Characteristics

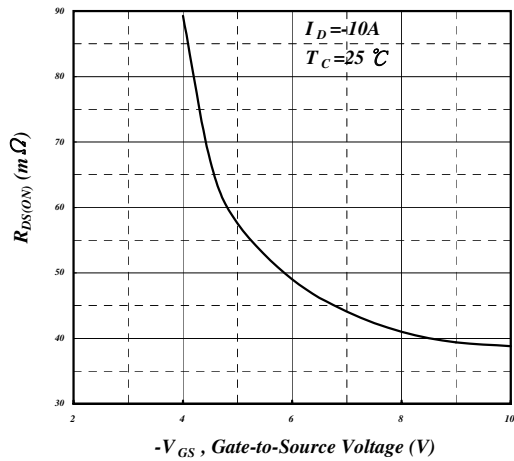


Fig 3. On-Resistance v.s. Gate Voltage

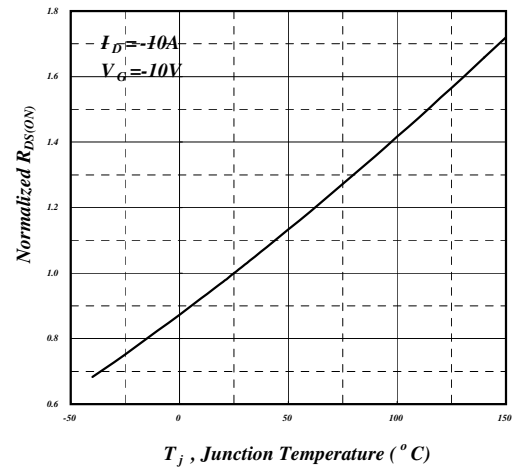


Fig 4. Normalized On-Resistance v.s. Junction Temperature

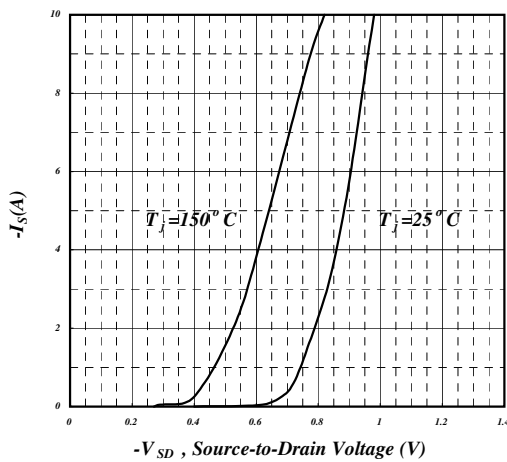


Fig5. Forward Characteristic of Reverse Diode

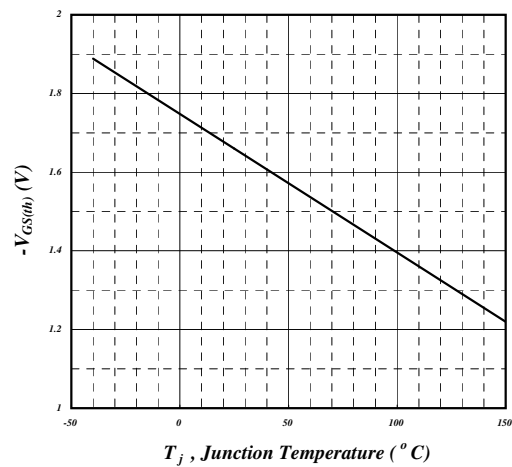


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

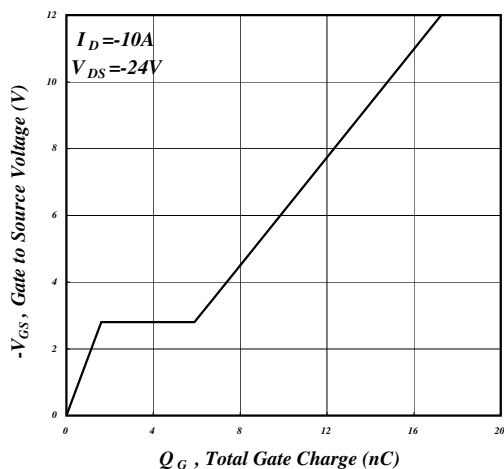


Fig 7. Gate Charge Characteristics

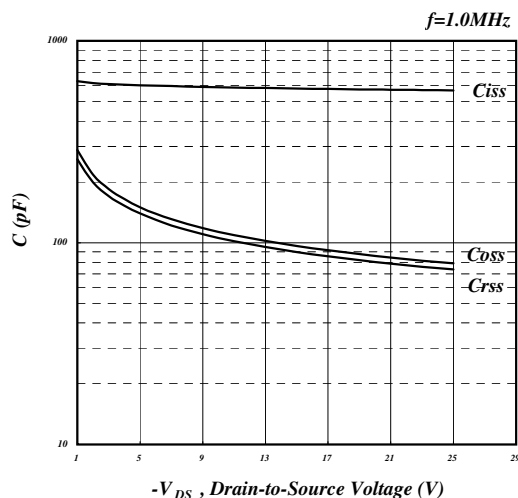


Fig 8. Typical Capacitance Characteristics

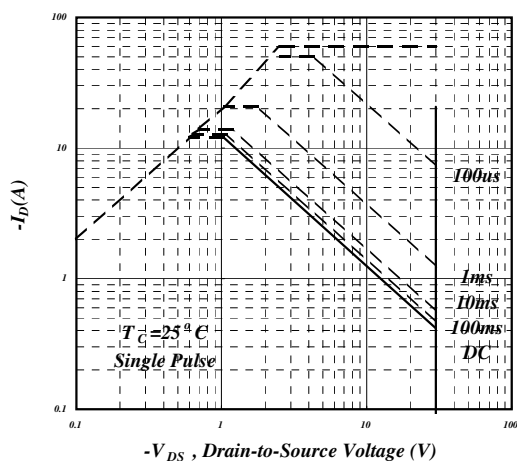


Fig 9. Maximum Safe Operating Area

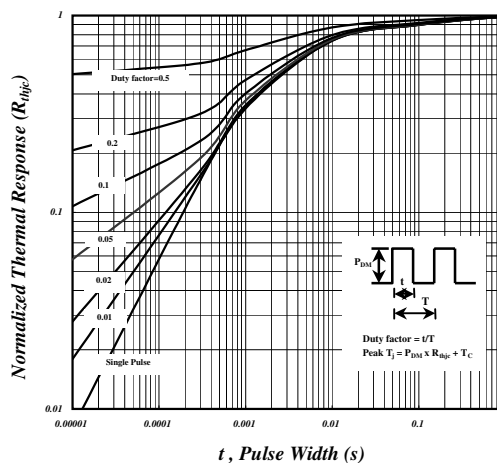


Fig 10. Effective Transient Thermal Impedance

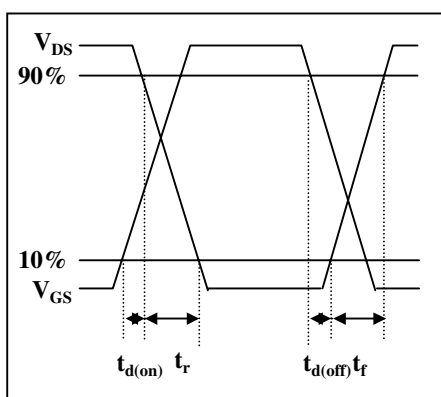


Fig 11. Switching Time Waveform

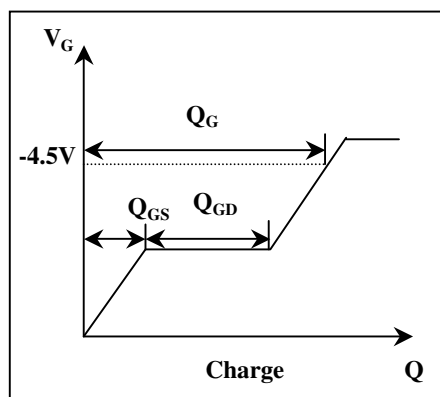


Fig 12. Gate Charge Waveform